



Silicon Power Schottky Diode

MBR12020CT thru MBR12040CTR

$V_{RRM} = 20\text{ V} - 100\text{ V}$

$I_F = 120\text{ A}$

Features

- High Surge Capability
- Types up to 100 V V_{RRM}

Twin Tower Package



Maximum ratings, at $T_j = 25\text{ °C}$, unless otherwise specified ("R" devices have leads reversed)

Parameter	Symbol	Conditions	MBR12020CT (R)	MBR12030CT (R)	MBR12035CT (R)	MBR12040CT (R)	Unit
Repetitive peak reverse voltage	V_{RRM}		20	30	35	40	V
RMS reverse voltage	V_{RMS}		14	21	25	28	V
DC blocking voltage	V_{DC}		20	30	35	40	V
Continuous forward current	I_F	$T_C \leq 140\text{ °C}$	120	120	120	120	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ °C}$, $t_p = 8.3\text{ ms}$	800	800	800	800	A
Operating temperature	T_j		-40 to 175	-40 to 175	-40 to 175	-40 to 175	°C
Storage temperature	T_{stg}		-40 to 175	-40 to 175	-40 to 175	-40 to 175	°C

Electrical characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	MBR12020CT (R)	MBR12030CT (R)	MBR12035CT (R)	MBR12060CT (R)	Unit
Diode forward voltage	V_F	$I_F = 60\text{ A}$, $T_j = 25\text{ °C}$	0.65	0.65	0.65	0.65	V
Reverse current	I_R	$V_R = 20\text{ V}$, $T_j = 25\text{ °C}$	3	3	3	3	mA
		$V_R = 20\text{ V}$, $T_j = 125\text{ °C}$	200	200	200	200	

Thermal characteristics

Thermal resistance, junction - case	R_{thJC}		0.8	0.8	0.8	0.8	°C/W
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America Semiconductor

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